

Attachment: Illustration of Non-Concurrent Supply of Impurities & Concurrent Supply of Impurities

FIG. A: Technique according to the present invention

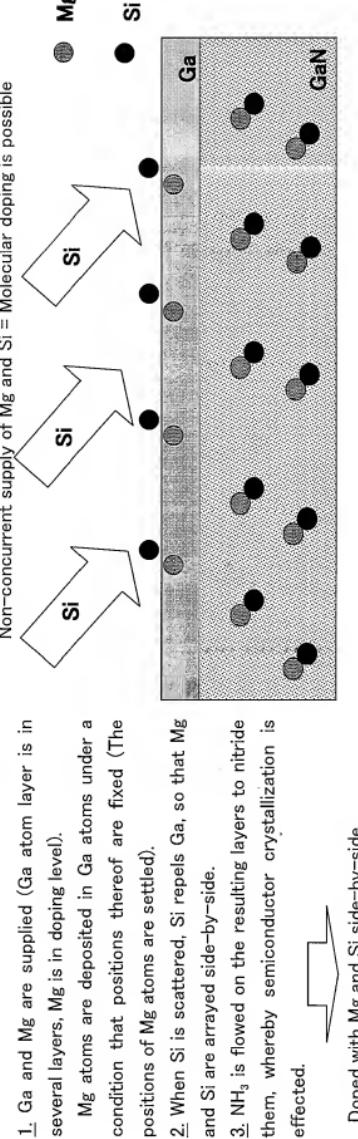


FIG. B: Technique according to Kobayashi

1. Ga is deposited (Ga atom layer is in several layers).

2. Si is supplied concurrently with Mg. Si and Mg are not arrayed side-by-side, but they are situated discretely.

3. NH₃ is flowed on the resulting layers to nitride them, whereby semiconductor crystallization is effected.



Concurrent supply of Mg and Si = Molecular doping is impossible

